

ABSTRACT OF THE DISCLOSURE

In a method of manufacturing a semiconductor device, after a lateral growth region 107 is formed by using a catalytic element for facilitating crystallization of silicon, the catalytic element is gettered into a phosphorus added region 108 by a heat treatment.

5 Thereafter, a gate insulating film 113 is formed to cover active layers 110 to 112 formed, and in this state, a thermal oxidation step is carried out. By this, the characteristics of an interface between the active layers and the gate insulating film can be improved while abnormal growth of a metal oxide is prevented.

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